WHAT IS CLAIMED IS:

1. A die with text deposited upon the die using semiconductor processing techniques, the die comprising:

a substrate which is cut from a wafer comprising a plurality of substrates;

a first paragraph in contact with the substrate; and

a second paragraph in contact with the substrate and aligned with the first paragraph in a column.

2. The die with text deposited upon the die using semiconductor processing techniques of claim 1, wherein:

the substrate is a semiconductor substrate; and

text in the column is comprised of one or more of a metal, an oxide, a polysemiconductor and a photoresist.

3. The die with text deposited upon the die using semiconductor processing techniques of claim 1, wherein the first and second paragraphs are comprised of a plurality of characters.

4. The die with text deposited upon the die using semiconductor processing techniques of claim 3, wherein each of the plurality of characters is comprised of a plurality of primitives.

5. The die with text deposited upon the die using semiconductor processing techniques of claim 1, the die further comprising:

a first character appearing in a first color; and

a second character appearing in a second color.

6. The die with text deposited upon the die using semiconductor processing techniques of claim 1, the die further comprising an image on the substrate.

7. A method for depositing a plurality of paragraphs of text on a substrate with semiconductor processing techniques, the method comprising:

reading a first paragraph from an electronic source;

reading a second paragraph from the electronic source;

positioning the first and second paragraphs into a column;

generating an electronic file at least partially representative of the column; and

imaging the substrate with the column, wherein the substrate is cut from a wafer having a plurality of substrates.

8. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 7, wherein the imaging the substrate includes lithographing the substrate with a mask.

9. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 7, the method further comprising:

converting a first character of the first paragraph into a first pattern;

converting a second character of the first paragraph into a second pattern; and

aligning the first and second characters on a line.

10. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 7, wherein the substrate is a semiconductor wafer.

11. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 7, the method further comprising determining an end of a first line in the first paragraph and beginning a second line.

12. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 7, the method further comprising determining an end of the first paragraph and beginning the second paragraph on the next line of the column.

13. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 7, the method further comprising detecting an end of a first column and depositing a next line in a second column.

14. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 7, the method further comprising:

determining a first color for a first character; and

determining a second color for a second character.

15. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 7, wherein the generating the electronic file comprises overlaying a silhouette over at least part of the column.

16. A lithographing system for depositing a plurality of paragraphs on a substrate, the lithographing system comprising:

a radiation source;

the substrate; and

a mask generated from an electronic file, wherein:

the mask is between the radiation source and the substrate, and

the mask includes a first and second paragraphs arranged in a column.

17. The lithographing system for depositing the plurality of paragraphs on the substrate as recited in claim 16, wherein the electronic file comprises a plurality of elements corresponding to characters for the plurality of paragraphs.

18. The lithographing system for depositing the plurality of paragraphs on the substrate as recited in claim 17, wherein each character of the first and second paragraphs is comprised of a plurality of rectangles wherein one side of the rectangle is equal in size to the process resolution.

19. The lithographing system for depositing the plurality of paragraphs on the substrate as recited in claim 16, wherein the first and second paragraphs are separated by at least one of: a hard return, a tab and an enlarged character.

20. The lithographing system for depositing the plurality of paragraphs on the substrate as recited in claim 16, the lithographing system further comprising:

a first character visible as a first color; and

a second character visible as a second color.

21. A method for depositing text and an image on a substrate with semiconductor processing techniques, the method comprising:

loading a phrase;

loading a silhouette image;

providing a mask file at least partially representative of the phrase and the silhouette image, wherein the generating step comprises overlaying a silhouette over at least part of the phrase; and

imaging the substrate with the electronic file.

22. The method for depositing text and the image on the substrate with semiconductor processing techniques as recited in claim 21, wherein the imaging the substrate includes lithographing the substrate with a mask.

23. The method for depositing text and the image on the substrate with semiconductor processing techniques as recited in claim 21, the method further comprising:

converting a first character of the phrase into a first pattern;

converting a second character of the phrase into a second pattern; and

aligning the first and second characters on a line.

24. The method for depositing text and the image on the substrate with semiconductor processing techniques as recited in claim 21, wherein the substrate is a semiconductor wafer.

25. The method for depositing text and the image on the substrate with semiconductor processing techniques as recited in claim 21, the method further comprising:

determining a first color for a first character; and

determining a second color for a second character.

26. A method for depositing a plurality of paragraphs of text on a substrate with semiconductor processing techniques, the method comprising:

reading a first paragraph from an electronic source;

reading a second paragraph from the electronic source;

positioning the first and second paragraphs into one or more columns;

generating an electronic file at least partially representative of the column; and

producing the column on the substrate using semiconductor processing techniques, wherein the substrate is cut from a wafer having a plurality of substrates.

27. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 26, wherein the producing step includes lithographing the substrate with a mask.

28. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 26, the method further comprising:

converting a first character of the first paragraph into a first pattern;

converting a second character of the first paragraph into a second pattern; and

aligning the first and second characters on a line.

29. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 26, wherein the substrate is a semiconductor wafer.

30. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 26, the method further

comprising determining an end of a first line in the first paragraph and beginning a second line.

31. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 26, the method further comprising determining an end of the first paragraph and beginning the second paragraph on the next line of the column.

32. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 26, the method further comprising detecting an end of a first column and depositing a next line in a second column.

33. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 26, the method further comprising:

determining a first color for a first character; and

determining a second color for a second character.

34. The method for depositing the plurality of paragraphs of text on the substrate with semiconductor processing techniques as recited in claim 26, wherein the generating the electronic file comprises overlaying a silhouette over at least part of the column.